



## 型号/TYPE: SLS8810

SLS8810采用先进的沟道技术,提供卓越的rds (on)和低栅极电荷。防静电。该装置适合用作单向或双向负荷开关通用漏极配置。

The SLS8810 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

## 主要特性/Features

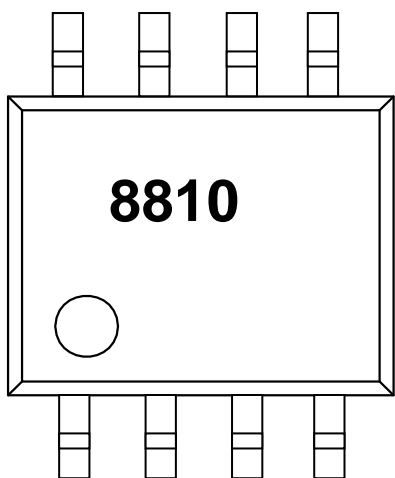
### N-CHANNEL

极低rds的超高密度单元设计 (开) Super high density cell design for extremely low RDS(ON)  
特殊电阻和最大直流电流能力 Exceptional on-resistance and maximum DC current capability

## 应用/Application

笔记本中的电源管理 Power Management in Note book  
便携式设备 Portable Equipment  
电池供电系统 Battery Powered System  
负荷开关 Load Switch

## 印字/MARKING 引脚定义/pin definition





**极限参数/Absolute maximum ratings(Ta=25°C)**

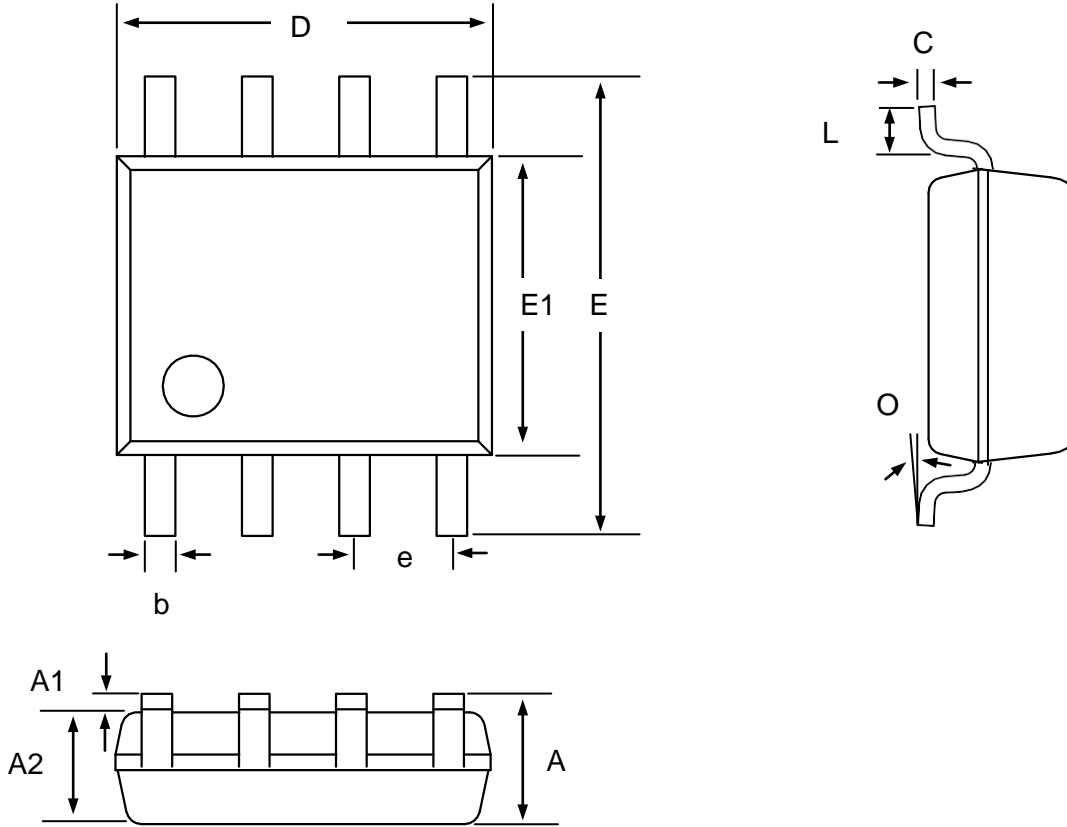
Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	VDS	17	V
Gate-Source Voltage	VGS	±10	V

**电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted )**

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BVDSS	Drain-Source Breakdown	VGS=0, ID=250μ A	17			V
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μ A	0.3		1.2	V
IGSS	Gate Body Leakage	VDS=0V, VGS=±8 V			±100	nA
IDSS	Zero Gate Voltage Drain	VDS=16V, VGS=0V			1	μ A
RDS(ON)	Drain-Source On-Resistance	VGS=4.5V, ID= 3.0A			28	mΩ
		VGS=2.5V, ID= 2.0A			38	



封装外观尺寸/SOP8 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270(BSC)		
E	3.800	3.900	4.000
E1	0.400	0.835	1.2700
L	0°	4°	8°